

FQP18N50V2/FQPF18N50V2 500V N-Channel MOSFET

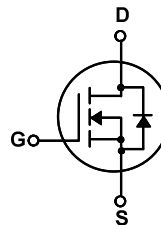
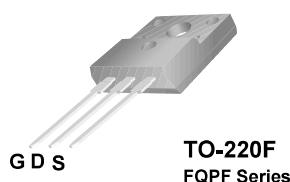
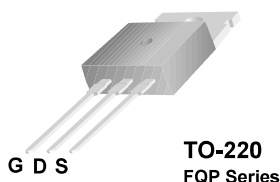
Features

- 550V @ $T_J = 150^\circ\text{C}$
- Typ. $R_{DS(on)} = 0.265\Omega$ @ $V_{GS} = 10\text{V}$
- Low gate charge (typical 42 nC)
- Low C_{rss} (typical 11 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficient switched mode power supplies, active power factor correction, electronic lamp ballast based on half bridge topology.



Absolute Maximum Ratings

Symbol	Parameter	FQP18N50V2	FQPF18N50V2	Units
V_{DSS}	Drain-Source Voltage	500		V
I_D	Drain Current	- Continuous ($T_C = 25^\circ\text{C}$)	18	18*
		- Continuous ($T_C = 100^\circ\text{C}$)	12.1	12.1*
I_{DM}	Drain Current - Pulsed (Note 1)	72	72*	A
V_{GSS}	Gate-Source Voltage	± 30		V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	330		mJ
I_{AR}	Avalanche Current (Note 1)	18		A
E_{AR}	Repetitive Avalanche Energy (Note 1)	25		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5		V/ns
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$)	208	69	W
		- Derate above 25°C	1.67	0.55
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150		$^\circ\text{C}$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300		$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	FQP18N50V2	FQPF18N50V2	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.6	1.8	$^\circ\text{C/W}$
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink	0.5	--	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	62.5	$^\circ\text{C/W}$

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
PV218N50	FQP18N50V2	TO-220	-	-	50
PFV218N50	FQPF18N50V2	TO-220F	-	-	50

Electrical Characteristics T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	500	--	--	V
ΔBV _{DSS} /ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C	--	0.5	--	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 500 V, V _{GS} = 0 V	--	--	1	μA
		V _{DS} = 400 V, T _C = 125°C	--	--	10	μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V	--	--	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V	--	--	-100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	3.0	--	5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 9 A	--	0.225	0.265	Ω
g _{FS}	Forward Transconductance	V _{DS} = 40 V, I _D = 9 A (Note 4)	--	16	--	S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz	--	2530	3290	pF
C _{oss}	Output Capacitance	V _{DS} = 400 V, V _{GS} = 0 V, f = 1.0 MHz	--	300	390	pF
C _{riss}	Reverse Transfer Capacitance		--	11	14.3	pF
C _{oss}	Output Capacitance	V _{DS} = 400 V, V _{GS} = 0 V, f = 1.0 MHz	--	76	--	pF
C _{oss eff.}	Effective Output Capacitance	V _{DS} = 0V to 400 V, V _{GS} = 0 V	--	150	--	pF
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DD} = 250 V, I _D = 18 A, R _G = 25 Ω (Note 4, 5)	--	40	90	ns
t _r	Turn-On Rise Time		--	150	310	ns
t _{d(off)}	Turn-Off Delay Time		--	95	200	ns
t _f	Turn-Off Fall Time		--	110	230	ns
Q _g	Total Gate Charge	V _{DS} = 400 V, I _D = 18 A, V _{GS} = 10 V (Note 4, 5)	--	42	55	nC
Q _{gs}	Gate-Source Charge		--	12	--	nC
Q _{gd}	Gate-Drain Charge		--	14	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	18	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	72	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 18 A	--	--	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 18 A, di _F / dt = 100 A/μs (Note 4)	--	420	--	ns
Q _{rr}	Reverse Recovery Charge		--	5.4	--	μC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. L = 1.83mH, I_{AS} = 18A, V_{DD} = 50V, R_G = 25 Ω, Starting T_J = 25°C
3. I_{SD} ≤ 18A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
4. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%
5. Essentially independent of operating temperature